



ASE GROUP

Vertical Integrated High Density Power Packaging Technology

CP Hung, Mark Li and Vikas Gupta

ASE Group

vikas.gupta@aseus.com



Outline

- **Technology Overview**
- **Power SiP Technologies**
 - aEASI
 - SESUB
 - Double Side SiP
 - 3D Power SiP
- **Integrated Power in u-Processor**
 - Advanced Packaging
 - Inductors
 - Capacitors
- **Summary**



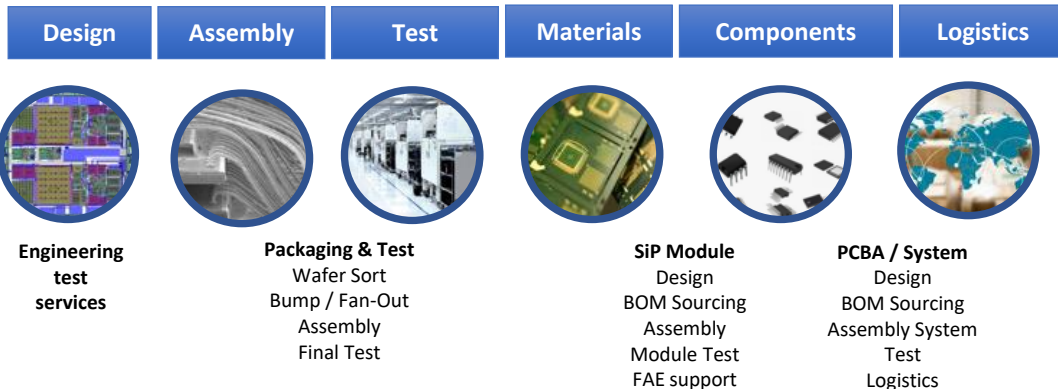
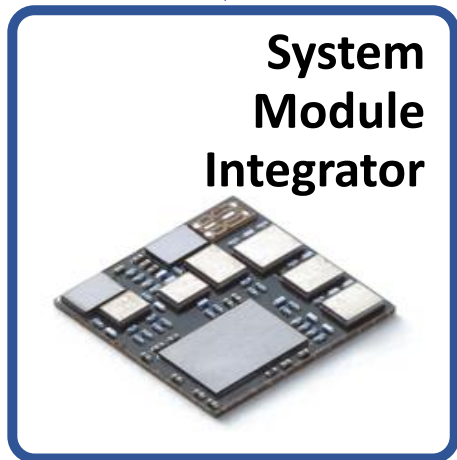
Application Integrated Solution



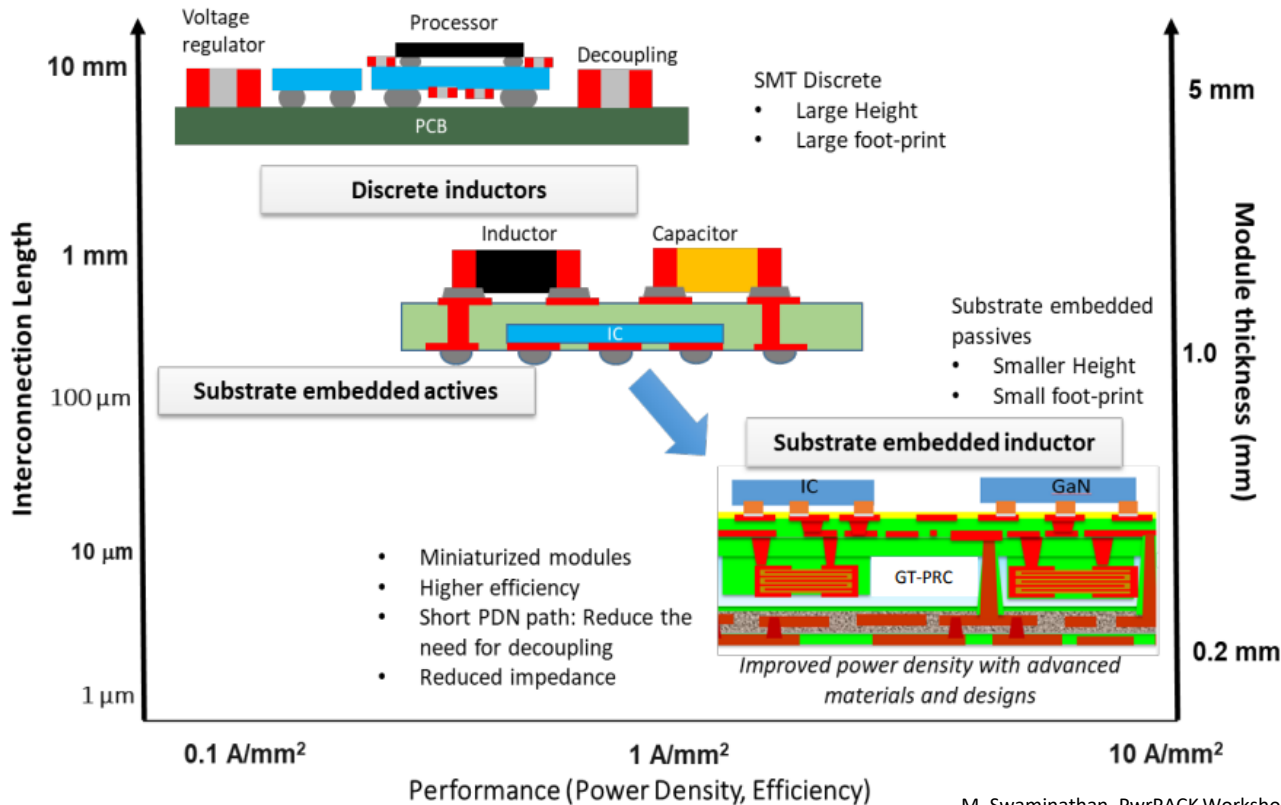
OSAT

Application-Specific

EMS



Power Delivery Trend



Focus of this presentation

1. Packaging technologies for miniaturization from board level to sub modules levels; higher efficiency and reduced impedance
2. Integrated power solutions encompassing 2.5/3D package configurations and high-performance passives

Outline

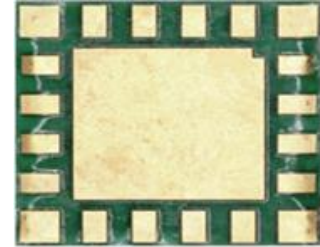
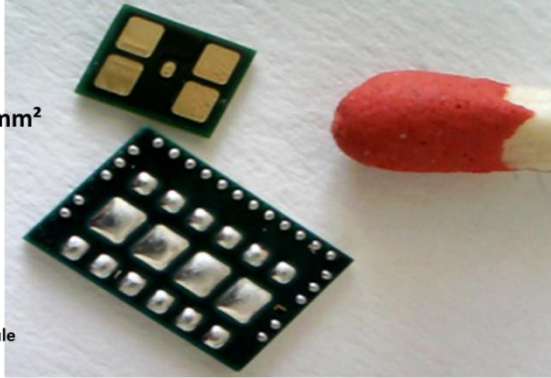
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aEASI (advanced EEmbedded Active System Integration)

MOSFET
3.4x3.0 mm²

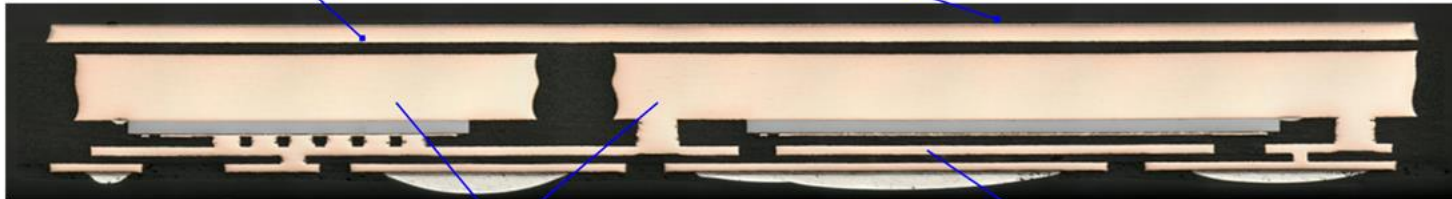
DC/DC Module
4.5x6.6 mm²



aEASI Size: 5 x 5 x 0.57 mm³ (exclude passives height)
1 Micro Power Chip with RDL: 2+1 Layer
Passives: 12 (0806 x 2, 0603 x 2, 0402 x 4, 0201 x 4)
>100KK units shipped

Good Thermal Dissipation with EMI Shielding

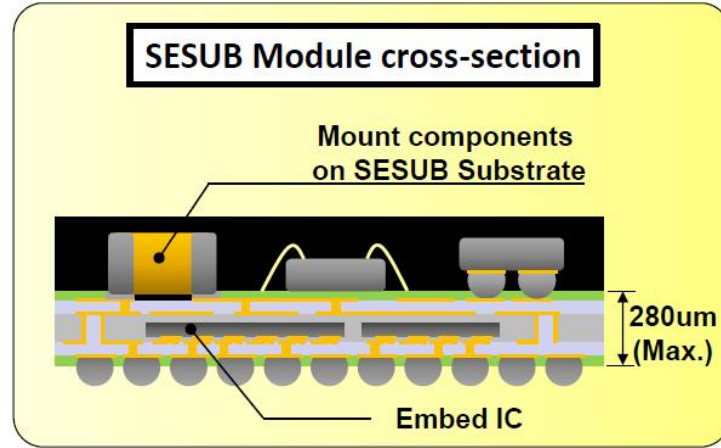
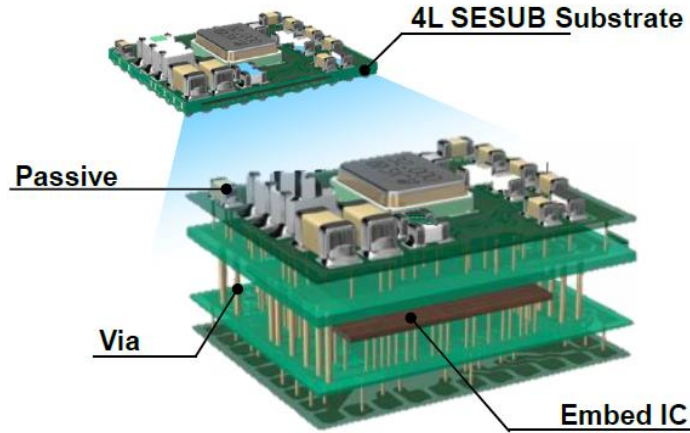
SMD on Top OK



Extreme Low R and L

Multiple RDL Layer

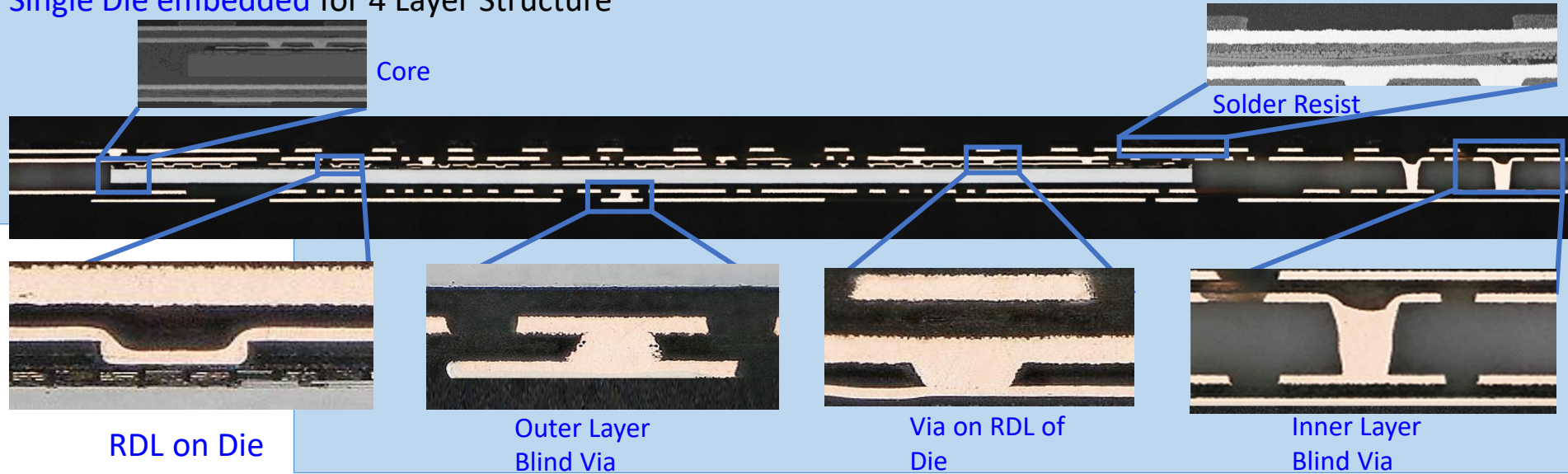
SESUB (Semiconductor EMBEDDED in SUBstrate)



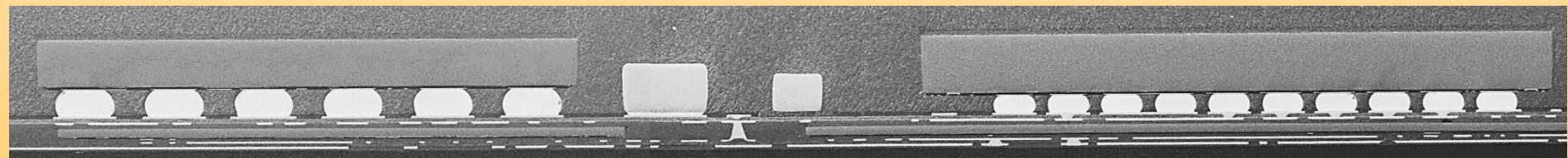
- IC wafer grinded to 50um and embedding in resin substrate
- Total substrate thickness 280um or below
- Multiple dies could be embedded in a SESUB

SESUB Construction (4 Layer)

Single Die embedded for 4 Layer Structure

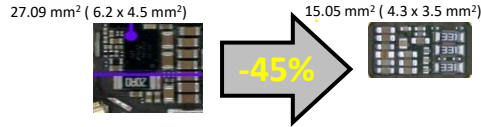


Two dies embedded in 4 Layer SESUB (2 WLPs and Passives on SESUB)

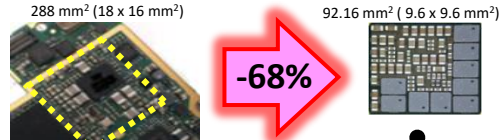


Embedded for Size Advantages

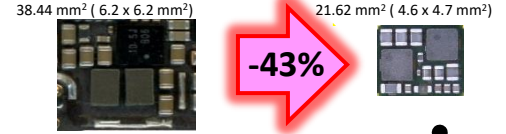
● Wireless Charge Rx



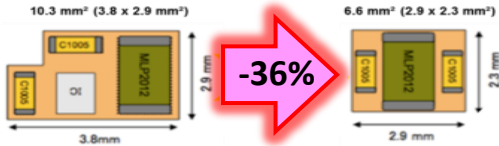
● Power Management Unit Module



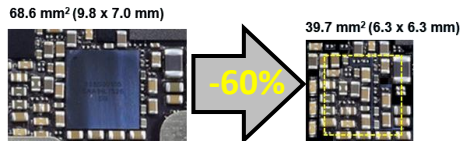
● Camera Power Module



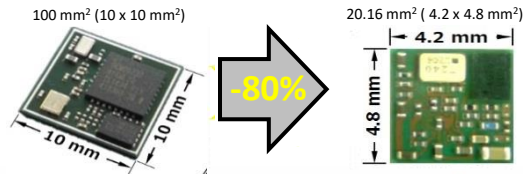
● μ DC-DC Converter Module



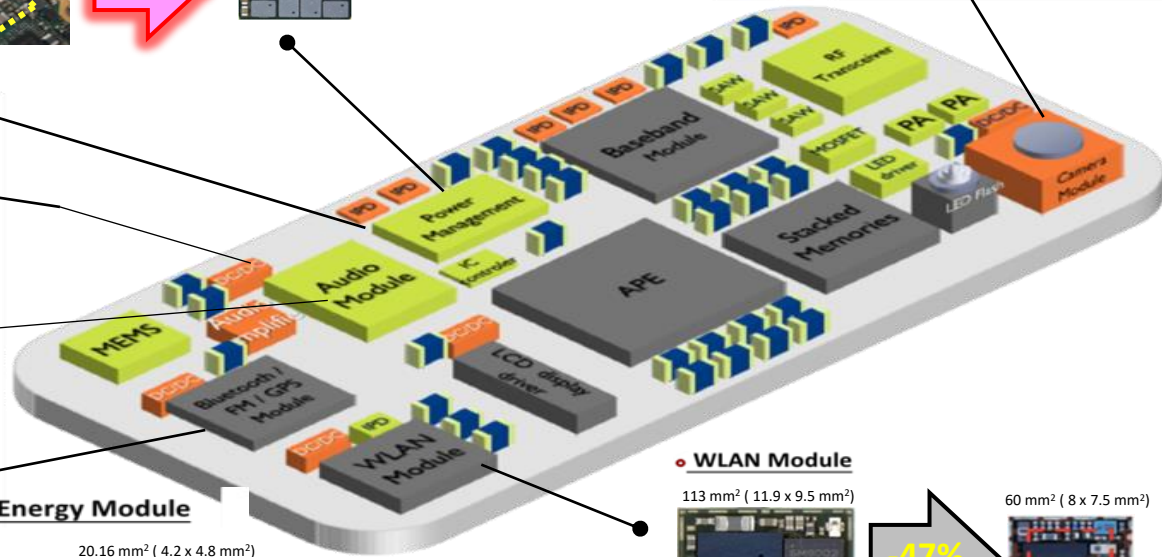
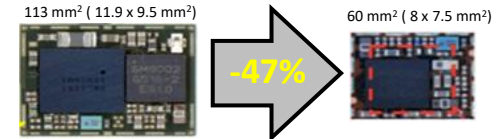
● Audio Module



● Bluetooth Low Energy Module

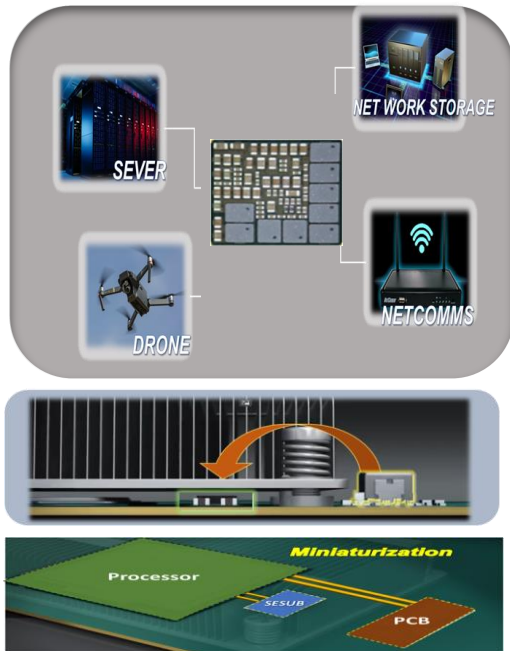


● WLAN Module



SESUB Applications and Production Summary

PMIC



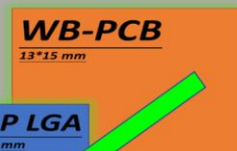
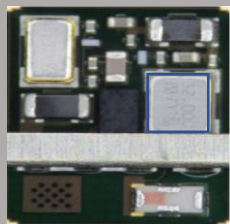
Consumer Application

● Camera Power Module

38.44 mm² (6.2 x 6.2 mm²)

21.62 mm² (4.6 x 4.7 mm²)

Area -43%



SESUB
5*6.5 mm

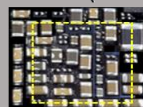
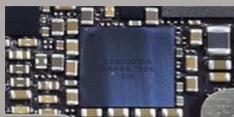
-80%

● Audio Module

68.6 mm² (9.8 x 7.0 mm)

39.7 mm² (6.3 x 6.3 mm)

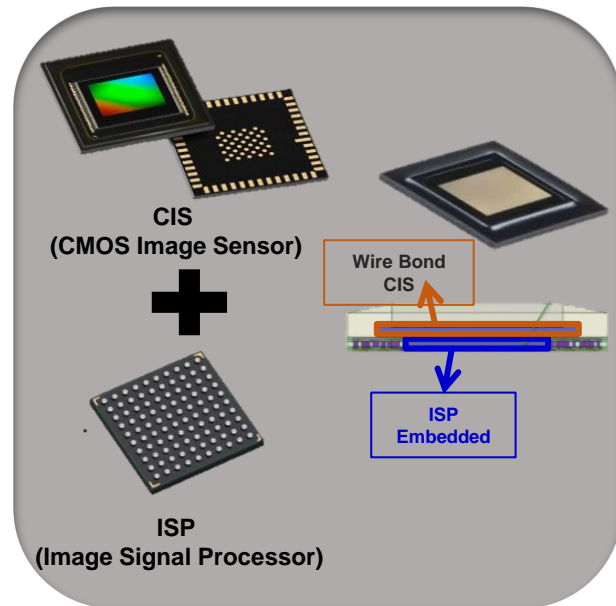
Area
~60%



- Miniaturization
- In HVM

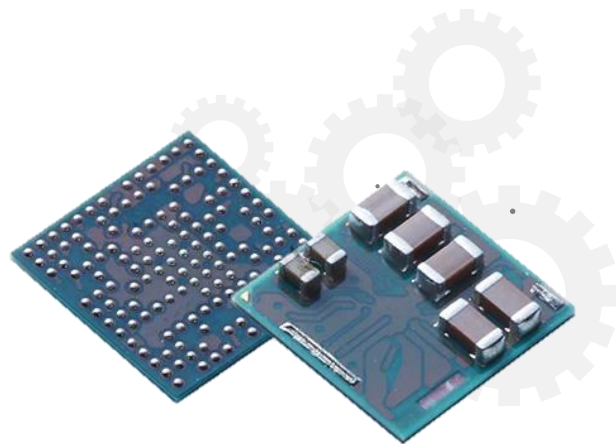
>50KK units shipped for each of the applications

Automotive



- Excellent signal performance
- Better thermal dissipation
- In HVM

SESUB Reliability Experience



Reliability



Precondition

TCT -65°C~150°C*5x
Baking 125°C*24hr
(MSL3)30°C/60% RH *192hr
Reflow 260°C*3x



uHAST

Temp:130°C , RH : 85%
Pressure: 33.3Psia, 96 hours



HTST

Temp: 150°C ,Time: 1000 hours



TCT

Temp:-55°C~125°C
mode: 1000/2000 cycles



PCT

Temp:121±2°C , ,100% RH,
Vapor pressure: 29.7Psia, Time: 96hr



Solderability

PC: Steam Aging B, Flux angle: 45
,Fluxtime:5~10s,
Temp:245±5°C,5±0.5s,
Rate: 25±6mm/s



LTST

Temp: -40°C,Time: 1000 hours

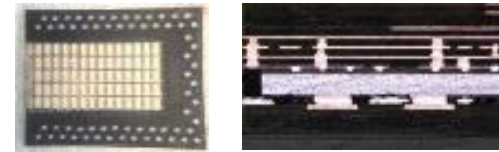
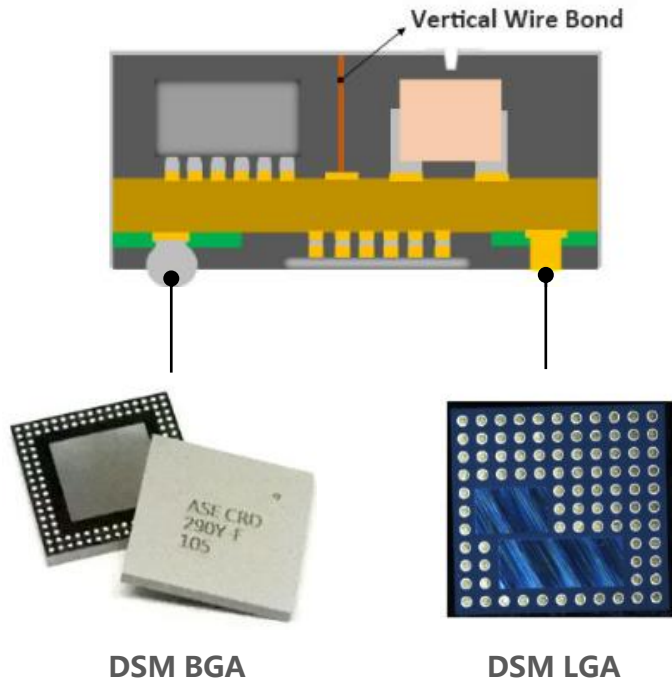


Multi Reflow

Temp: 260°C , 30 cycles



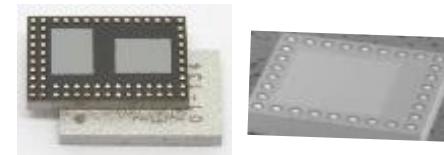
Double Side SiP



8.6x9.6x1.01mm
Thermal pad for high power design



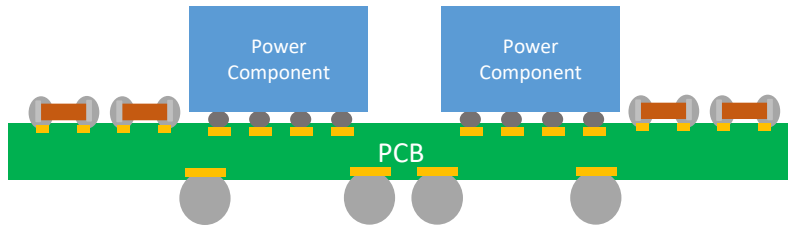
3.8x5.6x0.8mm
Laser ablation around ball



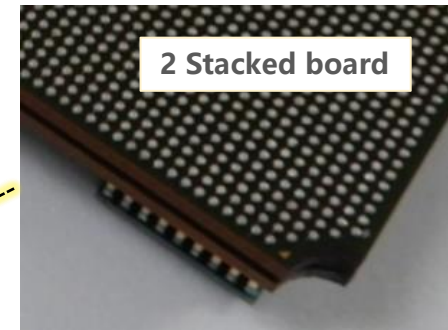
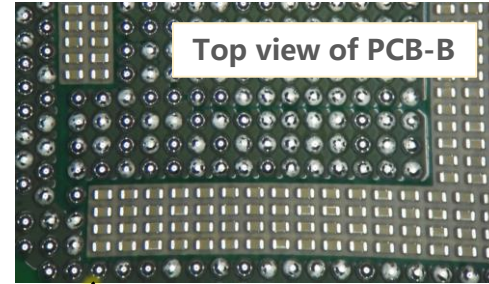
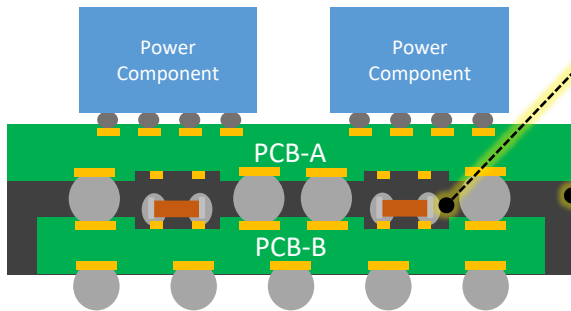
3.7x4.2x0.7mm
Grinding for thinning

- Double side reduced **20~40%** area
- DSM Low Profile < 0.8mm

3D Power SiP



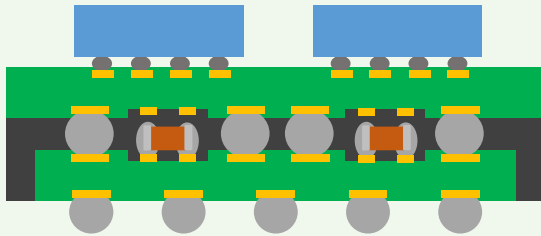
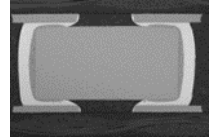
**Integrate Capacitors (>500ea) on PCB_B;
Assemble PCB_B on PCB_A**



- Enhance PDN performance
- Compact Size
- Mass production in 2023



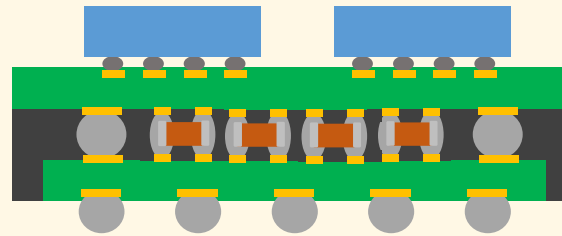
3D Power SiP Roadmap



3D Power SiP 1.0

- Connect Capacitors to Bottom PCB
- Enhance PDN performance
- Integrate capacitors (~500ea)

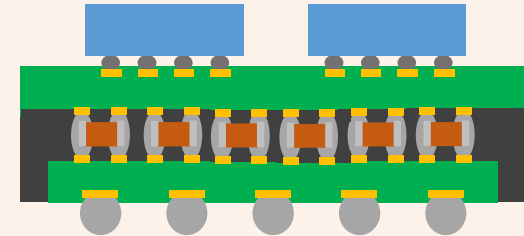
**In Qualification
Production 2023**



3D Power SiP 2.0

- Connect Capacitors to Top & Bottom PCB
- Further enhance PDN performance
- Integrate more capacitors (~1000ea)

In Development



3D Power SiP 3.0

- No solder ball between Top & Bottom PCB
- Better joint quality
- Integrate more capacitors (~1500ea)

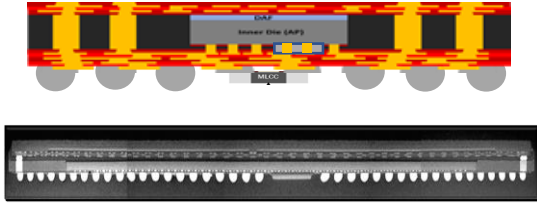
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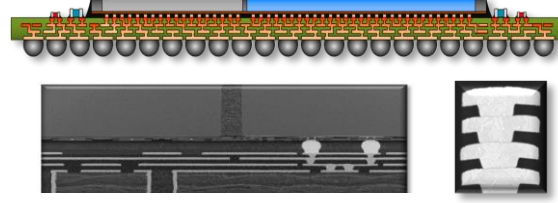
VIPack™ Platform – RDL Based Vertical Integration

VIPack™ Pillar I: FOPoP



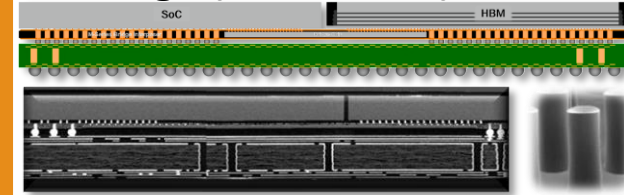
- Lowest Profile POP Package <330um
- Multiple RDL Routing Planes
- Balanced Construction
- Multi Die Capable for HI, DTC Integration

VIPack™ Pillar II: FOCoS



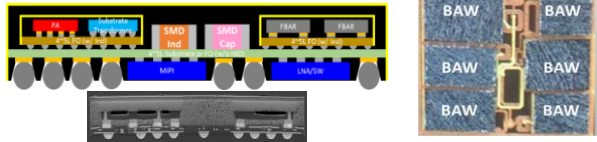
- High Density Fan-Out Single or Multi Die
- Chip First or Chip Last Integration
- 1.5/1.5um Line/Space, 6 metal layers, 32x38FO
- Flip Chip attached to RDL or Organic Substrate
- HBM Integration via RDL-Non-Bridge Die

VIPack™ Pillar III: FOCoS - Bridge (Embedded)



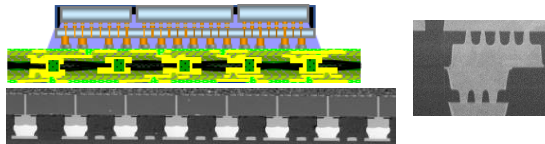
- Multi Die Attached to Both Sides of an RDL stack
- Bridge Die, DTC, VCO, etc. Integration
- Advanced HBM Integration & ASIC Disaggregation
- M-Series Integration Options

VIPack™ Pillar IV: FOSiP for RF Module



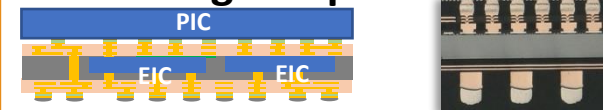
- Lowest Profile DS-SiP
- Multi- Pkg Integration
- Ultra High -Density Component Spacing
- Multi Layer RDL Stack w/Stacked Vias & integrated passives

VIPack™ Pillar V: 2.5D/3D IC



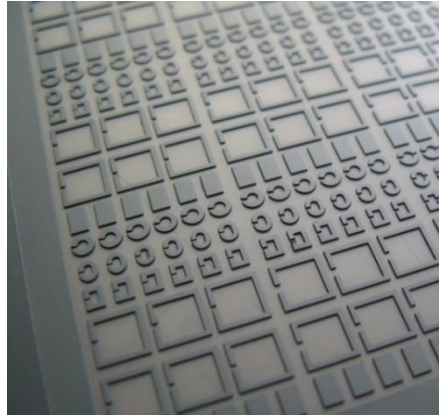
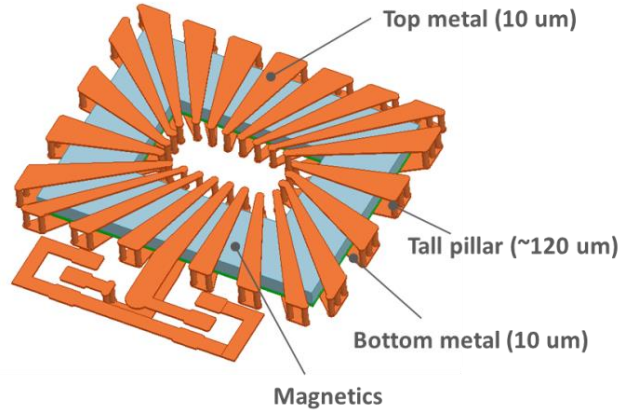
- Sticked interposer for large die area->1.6 reticle
- L/S <1um up to 5 layers
- 3D- TSV Last, MEOL, Hybrid Bond
- Integrated Passives in RDL

VIPack™ Pillar VI: Co-Packaged Optics

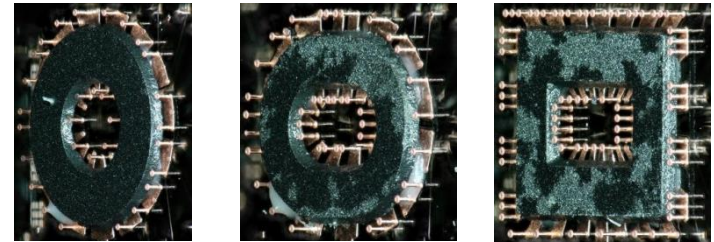
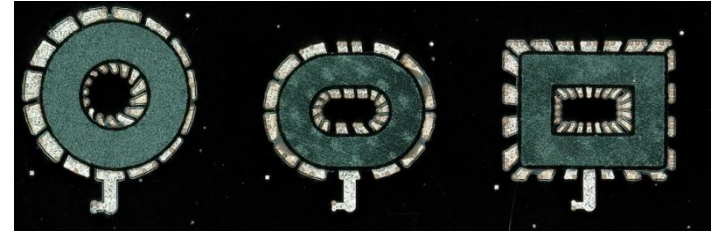


- Extends roadmap of SERDES HS Interface
- High Integration of PIC/EIC Die- Perf
- V-Groove Alignment DRIE
- Option- Embedded RDL for Die Integration

3D Tall Pillar Inductor

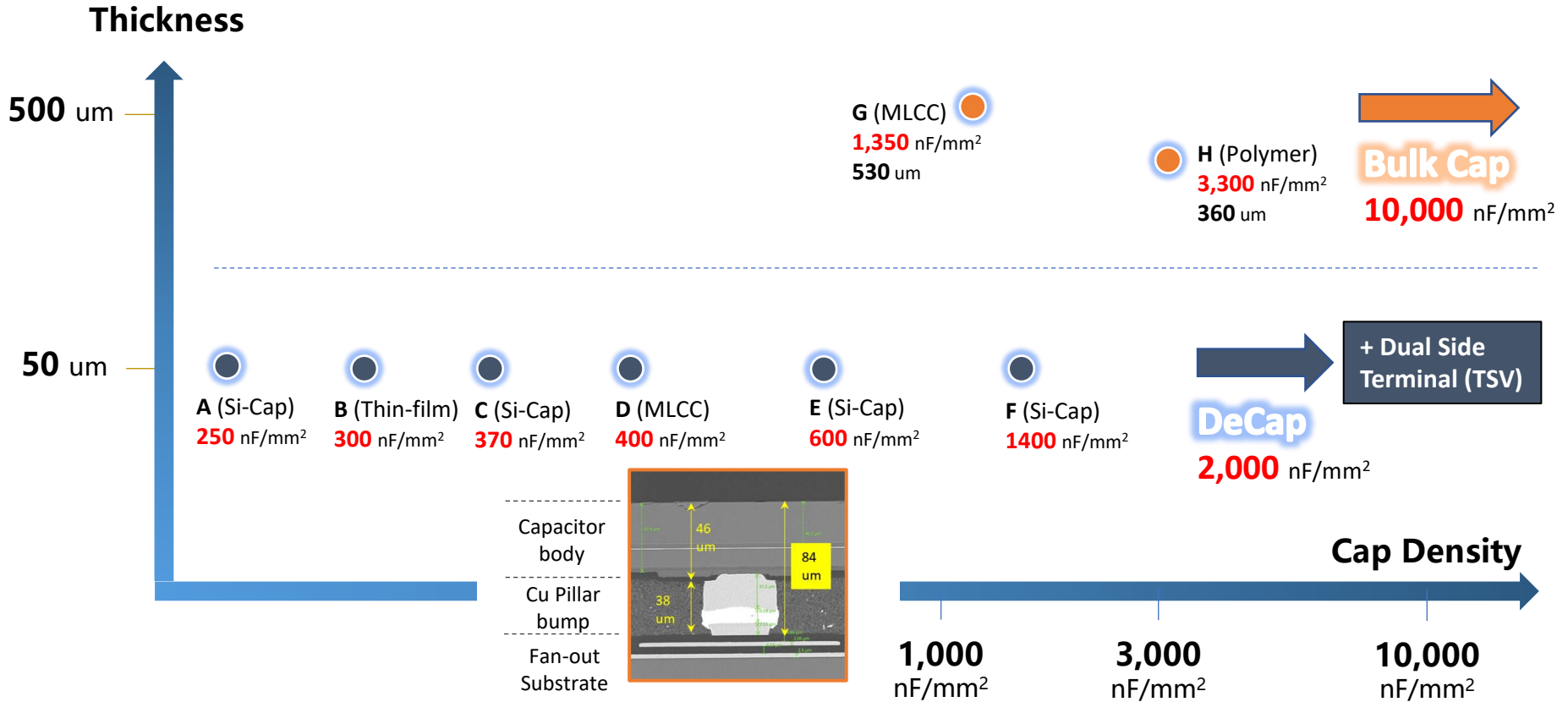


Magnetics from 3rd party

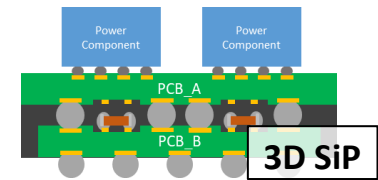
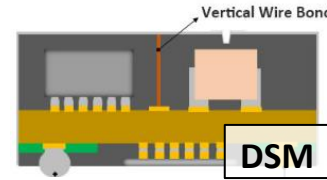
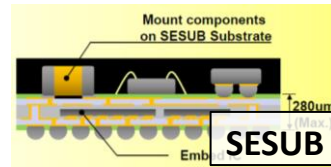


Top view and 3D view

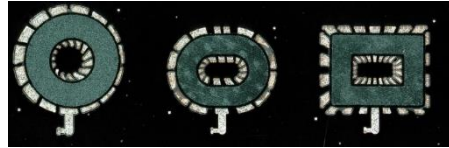
Capacitor Benchmark & Options



- High power density for wide array of applications through Vertical Power Integration using ASE SiP Technology

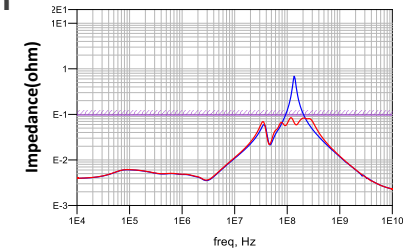
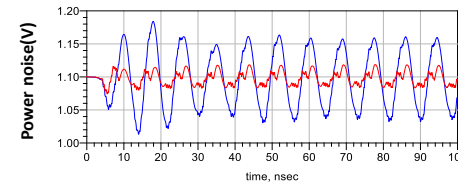
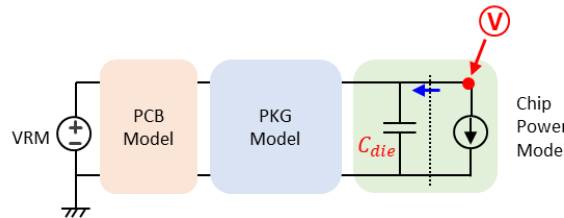


- Enabling 2.5D 3D package platforms (and associated PDK's) with integrated VR, Inductors, and Capacitors in collaboration with designers, passive component/ magnetic suppliers



Summary

- Coupled with co-design expertise to optimize package design including power integrity analysis, ball map and decoupling capacitor allocation



Thank You

**Acknowledgements:
Kay Essig, William Chen and Mark Gerber**



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日月光集團

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